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### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	3120
Total RAM Bits	36864
Number of I/O	212
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	281-TFBGA, CSBGA
Supplier Device Package	281-CSP (10x10)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/aglp125v5-cs281i">https://www.e-xfl.com/product-detail/microchip-technology/aglp125v5-cs281i</a>

The IGLOO PLUS family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the IGLOO PLUS family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/communications, computing, and avionics markets.

### **Firm-Error Immunity**

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of IGLOO PLUS flash-based FPGAs. Once it is programmed, the flash cell configuration element of IGLOO PLUS FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

### **Advanced Flash Technology**

The IGLOO PLUS family offers many benefits, including nonvolatility and reprogrammability, through an advanced flash-based, 130 nm LVCMOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

IGLOO PLUS family FPGAs utilize design and process techniques to minimize power consumption in all modes of operation.

### **Advanced Architecture**

The proprietary IGLOO PLUS architecture provides granularity comparable to standard-cell ASICs. The IGLOO PLUS device consists of five distinct and programmable architectural features (Figure 1-1 on page 1-4):

- Flash\*Freeze technology
- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory<sup>†</sup>
- Extensive CCCs and PLLs<sup>†</sup>
- Advanced I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the IGLOO PLUS core tile as either a three-input lookup table (LUT) equivalent or a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the ProASIC® family of third-generation-architecture flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

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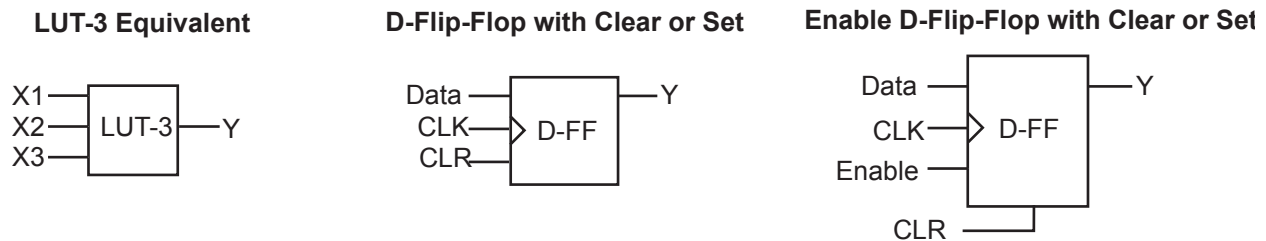
<sup>†</sup> The AGLP030 device does not support PLL or SRAM.

## VersaTiles

The IGLOO PLUS core consists of VersaTiles, which have been enhanced beyond the ProASIC<sup>PLUS</sup>® core tiles. The IGLOO PLUS VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set

Refer to [Figure 1-3](#) for VersaTile configurations.



**Figure 1-3 • VersaTile Configurations**

## User Nonvolatile FlashROM

IGLOO PLUS devices have 1 kbit of on-chip, user-accessible, nonvolatile FlashROM. The FlashROM can be used in diverse system applications:

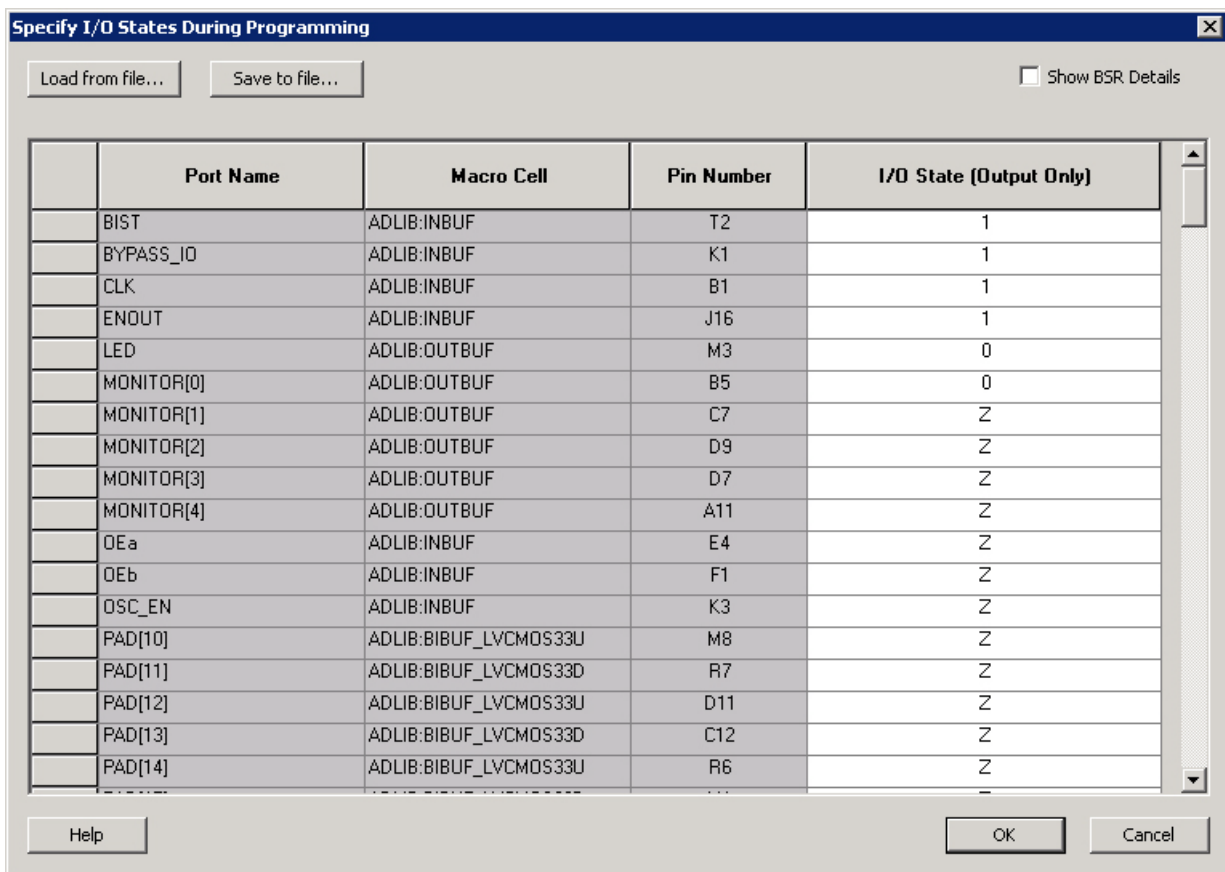
- Internet protocol addressing (wireless or fixed)
- System calibration settings
- Device serialization and/or inventory control
- Subscription-based business models (for example, set-top boxes)
- Secure key storage for secure communications algorithms
- Asset management/tracking
- Date stamping
- Version management

The FlashROM is written using the standard IGLOO PLUS IEEE 1532 JTAG programming interface. The core can be individually programmed (erased and written), and on-chip AES decryption can be used selectively to securely load data over public networks (except in AGLP030 devices), as in security keys stored in the FlashROM for a user design.

The FlashROM can be programmed via the JTAG programming interface, and its contents can be read back either through the JTAG programming interface or via direct FPGA core addressing. Note that the FlashROM can only be programmed from the JTAG interface and cannot be programmed from the internal logic array.

The FlashROM is programmed as 8 banks of 128 bits; however, reading is performed on a byte-by-byte basis using a synchronous interface. A 7-bit address from the FPGA core defines which of the 8 banks and which of the 16 bytes within that bank are being read. The three most significant bits (MSBs) of the FlashROM address determine the bank, and the four least significant bits (LSBs) of the FlashROM address define the byte.

The IGLOO PLUS development software solutions, Libero<sup>®</sup> System-on-Chip (SoC) and Designer, have extensive support for the FlashROM. One such feature is auto-generation of sequential programming files for applications requiring a unique serial number in each part. Another feature allows the inclusion of static data for system version control. Data for the FlashROM can be generated quickly and easily using Libero SoC and Designer software tools. Comprehensive programming file support is also included to allow for easy programming of large numbers of parts with differing FlashROM contents.



**Figure 1-4 • I/O States During Programming Window**

- Click OK to return to the FlashPoint – Programming File Generator window.

**Note:** I/O States During programming are saved to the ADB and resulting programming files after completing programming file generation.

### Package Thermal Characteristics

The device junction-to-case thermal resistivity is  $\theta_{jc}$  and the junction-to-ambient air thermal resistivity is  $\theta_{ja}$ . The thermal characteristics for  $\theta_{ja}$  are shown for two air flow rates. The maximum operating junction temperature is 100°C. EQ 2 shows a sample calculation of the maximum operating power dissipation allowed for a 484-pin FBGA package at commercial temperature and in still air.

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. (}^{\circ}\text{C)} - \text{Max. ambient temp. (}^{\circ}\text{C)}}{\theta_{ja} (^{\circ}\text{C/W)}} = \frac{100^{\circ}\text{C} - 70^{\circ}\text{C}}{20.5^{\circ}\text{C/W}} = 1.46 \text{ W}$$

EQ 2

**Table 2-5 • Package Thermal Resistivities**

Package Type	Device	Pin Count	$\theta_{jc}$	$\theta_{jb}$	$\theta_{ja}$			Unit
					Still Air	1 m/s	2.5 m/s	
Chip Scale Package (CSP)	AGLP030	CS201	-	-	46.3	-	-	C/W
	AGLP060	CS201	7.1	19.7	40.5	35.1	32.9	C/W
	AGLP060	CS289	13.9	34.1	48.7	43.5	41.9	C/W
	AGLP125	CS289	10.8	27.9	42.2	37.1	35.5	C/W
	AGLP125	CS281	11.3	17.6	-	-	-	C/W
Thin Quad Flat Package (VQ)	AGLP030	VQ128	18.0	50.0	56.0	49.0	47.0	C/W
	AGLP060	VQ176	21.0	55.0	58.0	52.0	50.0	C/W

### Temperature and Voltage Derating Factors

**Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays (normalized to  $T_J = 70^{\circ}\text{C}$ ,  $V_{CC} = 1.425 \text{ V}$ )**  
For IGLOO PLUS V2 or V5 devices, 1.5 V DC Core Supply Voltage

Array Voltage $V_{CC}$ (V)	Junction Temperature ( $^{\circ}\text{C}$ )					
	$-40^{\circ}\text{C}$	$0^{\circ}\text{C}$	$25^{\circ}\text{C}$	$70^{\circ}\text{C}$	$85^{\circ}\text{C}$	$100^{\circ}\text{C}$
1.425	0.934	0.953	0.971	1.000	1.007	1.013
1.5	0.855	0.874	0.891	0.917	0.924	0.929
1.575	0.799	0.816	0.832	0.857	0.864	0.868

**Table 2-7 • Temperature and Voltage Derating Factors for Timing Delays (normalized to  $T_J = 70^{\circ}\text{C}$ ,  $V_{CC} = 1.14 \text{ V}$ )**  
For IGLOO PLUS V2, 1.2 V DC Core Supply Voltage

Array Voltage $V_{CC}$ (V)	Junction Temperature ( $^{\circ}\text{C}$ )					
	$-40^{\circ}\text{C}$	$0^{\circ}\text{C}$	$25^{\circ}\text{C}$	$70^{\circ}\text{C}$	$85^{\circ}\text{C}$	$100^{\circ}\text{C}$
1.14	0.963	0.975	0.989	1.000	1.007	1.011
1.2	0.853	0.865	0.877	0.893	0.893	0.897
1.26	0.781	0.792	0.803	0.813	0.819	0.822

**Table 2-12 • Quiescent Supply Current (IDD), No IGLOO PLUS Flash\*Freeze Mode <sup>1</sup>**

	Core Voltage	AGLP030	AGLP060	AGLP125	Units
<b>ICCA Current <sup>2</sup></b>					
Typical (25°C)	1.2 V	6	10	13	μA
	1.5 V	16	20	28	μA
<b>ICCI or JTAG Current</b>					
VCCI / VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	μA
VCCI / VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	μA
VCCI / VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	μA
VCCI / VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	μA
VCCI / VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	μA

**Notes:**

1.  $IDD = N_{BANKS} * ICCI + ICCA$ . JTAG counts as one bank when powered.
2. Includes VCC, VCCPLL, and VPUMP currents.

## Power Consumption of Various Internal Resources

**Table 2-15 • Different Components Contributing to Dynamic Power Consumption in IGLOO PLUS Devices  
For IGLOO PLUS V2 or V5 Devices, 1.5 V Core Supply Voltage**

Parameter	Definition	Device Specific Dynamic Power (μW/MHz)		
		AGLP125	AGLP060	AGLP030
PAC1	Clock contribution of a Global Rib	4.489	2.696	0.000 <sup>1</sup>
PAC2	Clock contribution of a Global Spine	1.991	1.962	3.499
PAC3	Clock contribution of a VersaTile row	1.510	1.523	1.537
PAC4	Clock contribution of a VersaTile used as a sequential module	0.153	0.151	0.151
PAC5	First contribution of a VersaTile used as a sequential module	0.029	0.029	0.029
PAC6	Second contribution of a VersaTile used as a sequential module	0.323	0.323	0.323
PAC7	Contribution of a VersaTile used as a combinatorial module	0.280	0.300	0.278
PAC8	Average contribution of a routing net	1.097	1.081	1.130
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-13 on page 2-9.		
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-14 on page 2-9.		
PAC11	Average contribution of a RAM block during a read operation	25.00		
PAC12	Average contribution of a RAM block during a write operation	30.00		
PAC13	Dynamic contribution for PLL	2.70		

**Note:** 1. There is no Center Global Rib present in AGLP030, and thus it starts directly at the spine resulting in 0μW/MHz.

**Table 2-16 • Different Components Contributing to the Static Power Consumption in IGLOO PLUS Devices  
For IGLOO PLUS V2 or V5 Devices, 1.5 V Core Supply Voltage**

Parameter	Definition	Device-Specific Static Power (mW)		
		AGLP125	AGLP060	AGLP030
PDC1	Array static power in Active mode	See Table 2-12 on page 2-8		
PDC2	Array static power in Static (Idle) mode	See Table 2-11 on page 2-7		
PDC3	Array static power in Flash*Freeze mode	See Table 2-9 on page 2-7		
PDC4	Static PLL contribution	1.84 <sup>1</sup>		
PDC5	Bank quiescent power (VCCI-dependent)	See Table 2-12 on page 2-8		

**Notes:**

1. This is the minimum contribution of the PLL when operating at lowest frequency.
2. For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or the SmartPower tool in Libero SoC software.

- Bit 0 (LSB) = 100%
- Bit 1 = 50%
- Bit 2 = 25%
- ...
- Bit 7 (MSB) = 0.78125%
- Average toggle rate =  $(100\% + 50\% + 25\% + 12.5\% + \dots + 0.78125\%) / 8$

**Enable Rate Definition**

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

**Table 2-19 • Toggle Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
$\alpha_1$	Toggle rate of VersaTile outputs	10%
$\alpha_2$	I/O buffer toggle rate	10%

**Table 2-20 • Enable Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
$\beta_1$	I/O output buffer enable rate	100%
$\beta_2$	RAM enable rate for read operations	12.5%
$\beta_3$	RAM enable rate for write operations	12.5%



**Table 2-25 • Summary of I/O Timing Characteristics—Software Default Settings, STD Speed Grade,  
Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 3.0\text{ V}$**

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option <sup>1</sup>	Slew Rate	Capacitive Load (pF)	External Resistor ( $\Omega$ )	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{PYS}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	Units
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	12 mA	High	5 pF	–	0.97	1.76	0.18	0.85	1.15	0.66	1.80	1.39	2.20	2.64	ns
3.3 V LVCMOS Wide Range <sup>2</sup>	100 $\mu\text{A}$	12 mA	High	5 pF	–	0.97	2.47	0.18	1.18	1.64	0.66	2.48	1.91	3.16	3.76	ns
2.5 V LVCMOS	12 mA	12 mA	High	5 pF	–	0.97	1.77	0.18	1.06	1.22	0.66	1.81	1.51	2.22	2.56	ns
1.8 V LVCMOS	8 mA	8 mA	High	5 pF	–	0.97	2.00	0.18	1.00	1.43	0.66	2.04	1.76	2.29	2.55	ns
1.5 V LVCMOS	4 mA	4 mA	High	5 pF	–	0.97	2.29	0.18	1.16	1.62	0.66	2.33	2.00	2.37	2.57	ns

**Notes:**

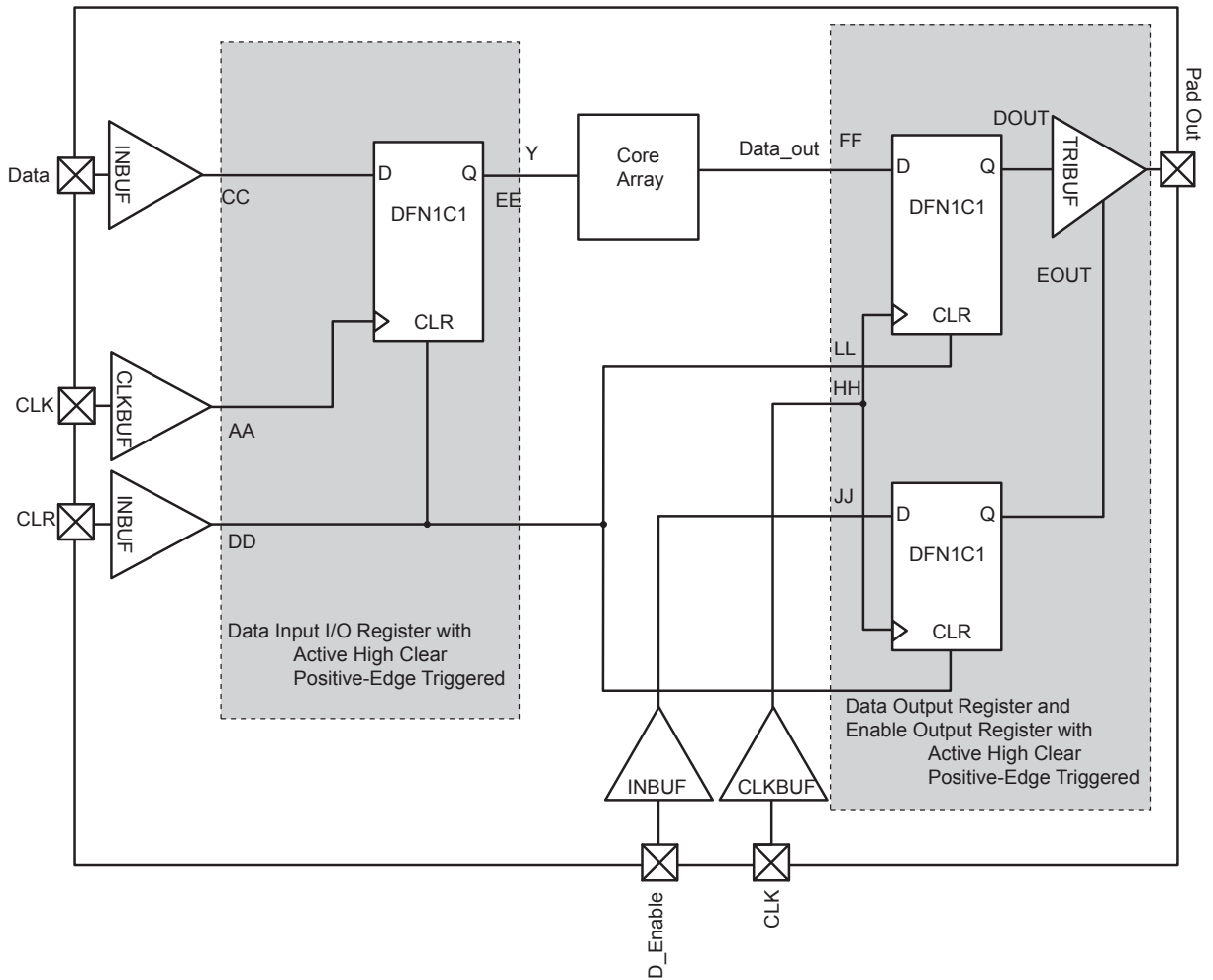
1. Note that 3.3 V LVCMOS wide range is applicable to 100  $\mu\text{A}$  drive strength only. The configuration will not operate at the equivalent software default drive strength. These values are for normal ranges only.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-72 • Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
$t_{OCLKQ}$	Clock-to-Q of the Output Data Register	H, DOUT
$t_{OSUD}$	Data Setup Time for the Output Data Register	F, H
$t_{OHD}$	Data Hold Time for the Output Data Register	F, H
$t_{OPRE2Q}$	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
$t_{OECLKQ}$	Clock-to-Q of the Output Enable Register	H, EOUT
$t_{OESUD}$	Data Setup Time for the Output Enable Register	J, H
$t_{OEHD}$	Data Hold Time for the Output Enable Register	J, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
$t_{iCLKQ}$	Clock-to-Q of the Input Data Register	A, E
$t_{iSUD}$	Data Setup Time for the Input Data Register	C, A
$t_{iHD}$	Data Hold Time for the Input Data Register	C, A
$t_{iPRE2Q}$	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{iREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{iRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

*Note:* \*See Figure 2-12 on page 2-41 for more information.

## Fully Registered I/O Buffers with Asynchronous Clear



**Figure 2-13 • Timing Model of the Registered I/O Buffers with Asynchronous Clear**

### 1.2 V DC Core Voltage

**Table 2-79 • Output Enable Register Propagation Delays**  
Commercial-Case Conditions:  $T_J = 70^{\circ}\text{C}$ , Worst-Case  $V_{CC} = 1.14\text{ V}$

Parameter	Description	Std.	Units
$t_{OECLKQ}$	Clock-to-Q of the Output Enable Register	1.06	ns
$t_{OESUD}$	Data Setup Time for the Output Enable Register	0.52	ns
$t_{OEHD}$	Data Hold Time for the Output Enable Register	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	1.25	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	1.36	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.24	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.24	ns
$t_{OEWCCLR}$	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OEWPPE}$	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.31	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.28	ns

*Note:* For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-6](#) for derating values.

## Embedded SRAM and FIFO Characteristics

### SRAM

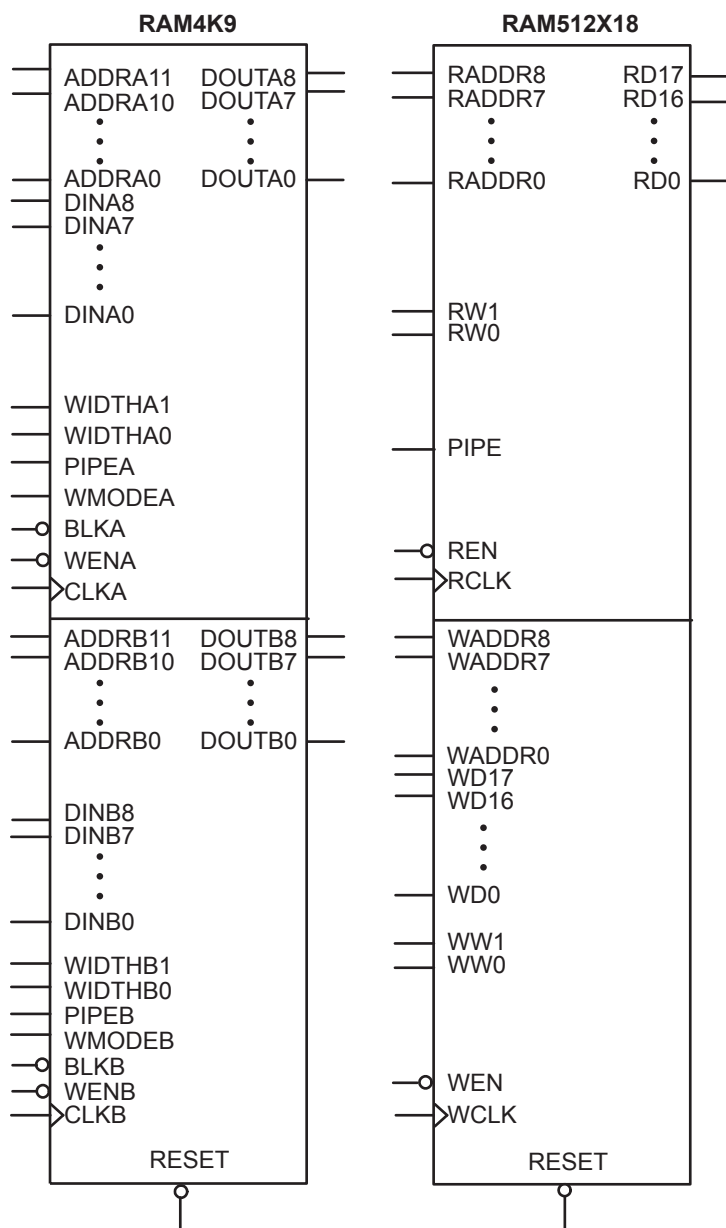
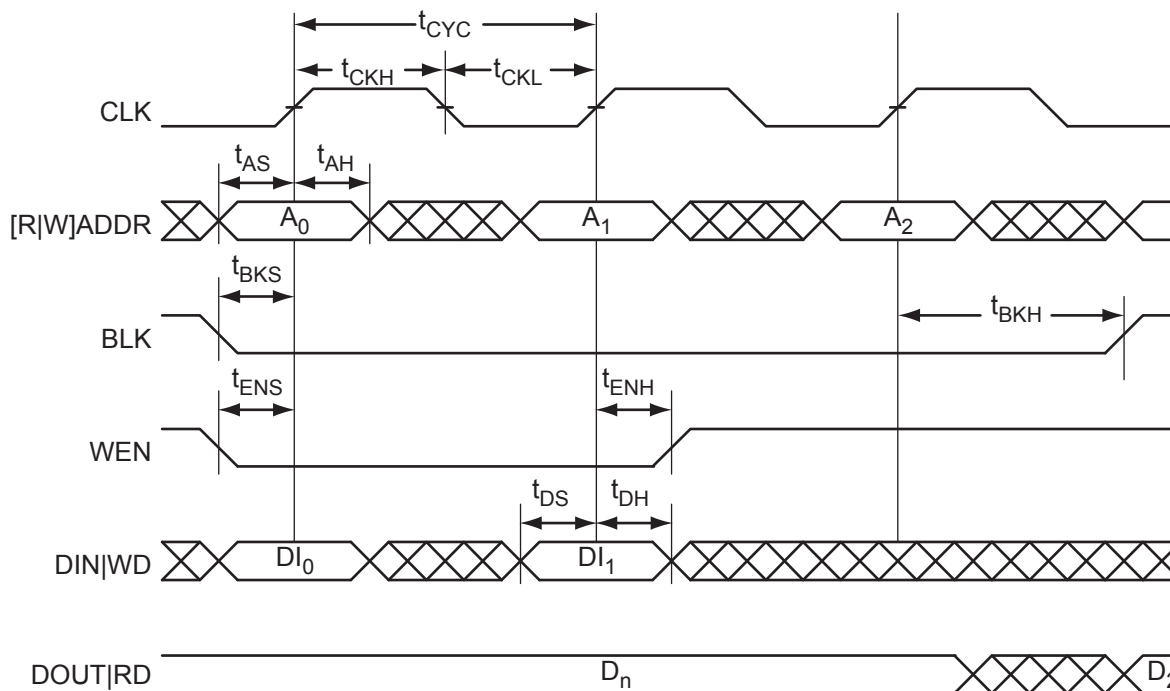
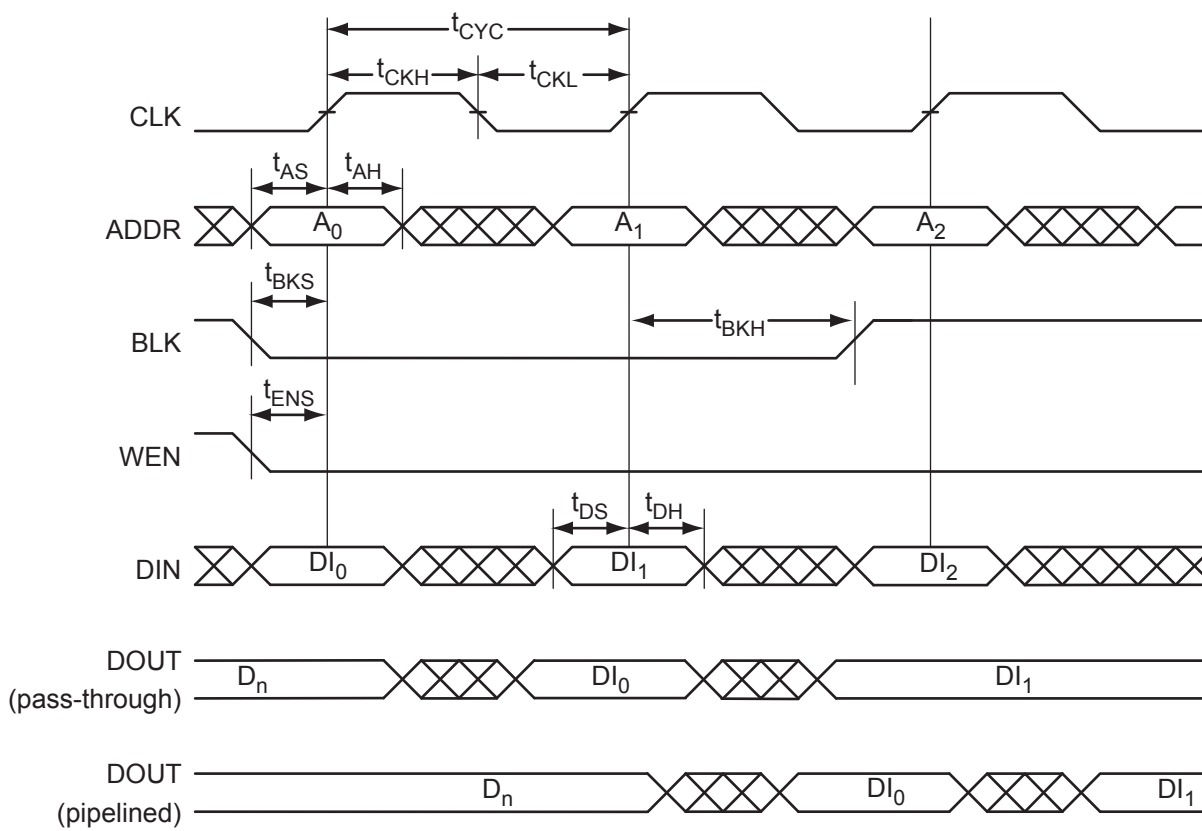


Figure 2-23 • RAM Models



**Figure 2-26 • RAM Write, Output Retained. Applicable to Both RAM4K9 and RAM512x18.**



**Figure 2-27 • RAM Write, Output as Write Data (WMODE = 1). Applicable to RAM4K9 only.**

## Timing Characteristics

### 1.5 V DC Core Voltage

**Table 2-96 • FIFO**
**Worst Commercial-Case Conditions:  $T_J = 70^{\circ}\text{C}$ ,  $V_{CC} = 1.425\text{ V}$** 

Parameter	Description	Std.	Units
$t_{\text{ENS}}$	REN, WEN Setup Time	1.66	ns
$t_{\text{ENH}}$	REN, WEN Hold Time	0.13	ns
$t_{\text{BKS}}$	BLK Setup Time	0.30	ns
$t_{\text{BKH}}$	BLK Hold Time	0.00	ns
$t_{\text{DS}}$	Input Data (WD) Setup Time	0.63	ns
$t_{\text{DH}}$	Input Data (WD) Hold Time	0.20	ns
$t_{\text{CKQ1}}$	Clock High to New Data Valid on RD (flow-through)	2.77	ns
$t_{\text{CKQ2}}$	Clock High to New Data Valid on RD (pipelined)	1.50	ns
$t_{\text{RCKEF}}$	RCLK High to Empty Flag Valid	2.94	ns
$t_{\text{WCKFF}}$	WCLK High to Full Flag Valid	2.79	ns
$t_{\text{CKAF}}$	Clock High to Almost Empty/Full Flag Valid	10.71	ns
$t_{\text{RSTFG}}$	RESET Low to Empty/Full Flag Valid	2.90	ns
$t_{\text{RSTAF}}$	RESET Low to Almost Empty/Full Flag Valid	10.60	ns
$t_{\text{RSTBQ}}$	RESET Low to Data Out Low on RD (flow-through)	1.68	ns
	RESET Low to Data Out Low on RD (pipelined)	1.68	ns
$t_{\text{REMRSTB}}$	RESET Removal	0.51	ns
$t_{\text{RECRSTB}}$	RESET Recovery	2.68	ns
$t_{\text{MPWRSTB}}$	RESET Minimum Pulse Width	0.68	ns
$t_{\text{CYC}}$	Clock Cycle Time	6.24	ns
$F_{\text{MAX}}$	Maximum Frequency for FIFO	160	MHz

*Note:* For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

## Embedded FlashROM Characteristics

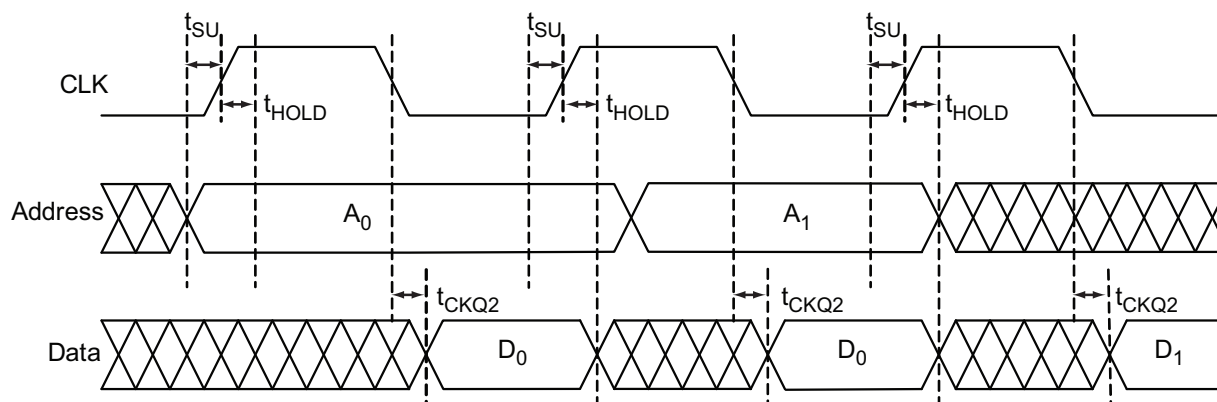


Figure 2-37 • Timing Diagram

### Timing Characteristics

#### 1.5 V DC Core Voltage

Table 2-98 • Embedded FlashROM Access Time

Worst Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
$t_{SU}$	Address Setup Time	0.57	ns
$t_{HOLD}$	Address Hold Time	0.00	ns
$t_{CK2Q}$	Clock to Out	17.58	ns
$F_{MAX}$	Maximum Clock Frequency	15	MHz

#### 1.2 V DC Core Voltage

Table 2-99 • Embedded FlashROM Access Time

Worst Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.14\text{ V}$

Parameter	Description	Std.	Units
$t_{SU}$	Address Setup Time	0.59	ns
$t_{HOLD}$	Address Hold Time	0.00	ns
$t_{CK2Q}$	Clock to Out	30.94	ns
$F_{MAX}$	Maximum Clock Frequency	10	MHz



VQ176	
Pin Number	AGLP060 Function
105	IO62RSB1
106	IO61RSB1
107	GCC2/IO60RSB1
108	GCB2/IO59RSB1
109	GCA2/IO58RSB1
110	GCA0/IO57RSB1
111	GCA1/IO56RSB1
112	VCCIB1
113	GND
114	GCB0/IO55RSB1
115	GCB1/IO54RSB1
116	GCC0/IO53RSB1
117	GCC1/IO52RSB1
118	IO51RSB1
119	IO50RSB1
120	VCC
121	IO48RSB1
122	IO47RSB1
123	IO45RSB1
124	IO44RSB1
125	IO43RSB1
126	VCCIB1
127	GND
128	GBC2/IO40RSB1
129	IO39RSB1
130	GBB2/IO38RSB1
131	IO37RSB1
132	GBA2/IO36RSB1
133	GBA1/IO35RSB0
134	NC
135	GBA0/IO34RSB0
136	NC
137	GBB1/IO33RSB0
138	NC
139	GBC1/IO31RSB0

VQ176	
Pin Number	AGLP060 Function
140	GBB0/IO32RSB0
141	GBC0/IO30RSB0
142	IO29RSB0
143	IO28RSB0
144	IO27RSB0
145	VCCIB0
146	GND
147	IO26RSB0
148	IO25RSB0
149	IO24RSB0
150	IO23RSB0
151	IO22RSB0
152	IO21RSB0
153	IO20RSB0
154	IO19RSB0
155	IO18RSB0
156	VCC
157	IO17RSB0
158	IO16RSB0
159	IO15RSB0
160	IO14RSB0
161	IO13RSB0
162	IO12RSB0
163	IO11RSB0
164	IO10RSB0
165	IO09RSB0
166	VCCIB0
167	GND
168	IO07RSB0
169	IO08RSB0
170	GAC1/IO05RSB0
171	IO06RSB0
172	GAB1/IO03RSB0
173	GAC0/IO04RSB0
174	GAB0/IO02RSB0

VQ176	
Pin Number	AGLP060 Function
175	GAA1/IO01RSB0
176	GAA0/IO00RSB0

CS289	
Pin Number	AGLP030 Function
A1	IO03RSB0
A2	NC
A3	NC
A4	GND
A5	IO10RSB0
A6	IO14RSB0
A7	IO16RSB0
A8	IO18RSB0
A9	GND
A10	IO23RSB0
A11	IO27RSB0
A12	NC
A13	NC
A14	GND
A15	NC
A16	NC
A17	IO30RSB0
B1	IO01RSB0
B2	GND
B3	NC
B4	NC
B5	IO07RSB0
B6	NC
B7	VCCIB0
B8	IO17RSB0
B9	IO19RSB0
B10	IO24RSB0
B11	IO28RSB0
B12	VCCIB0
B13	NC
B14	NC
B15	NC
B16	IO31RSB0
B17	GND
C1	NC
C2	IO00RSB0
C3	IO04RSB0

CS289	
Pin Number	AGLP030 Function
C4	NC
C5	VCCIB0
C6	IO09RSB0
C7	IO13RSB0
C8	IO15RSB0
C9	IO21RSB0
C10	GND
C11	IO29RSB0
C12	NC
C13	NC
C14	NC
C15	GND
C16	IO34RSB0
C17	NC
D1	NC
D2	IO119RSB3
D3	GND
D4	IO02RSB0
D5	NC
D6	NC
D7	NC
D8	GND
D9	IO20RSB0
D10	IO25RSB0
D11	NC
D12	NC
D13	GND
D14	IO32RSB0
D15	IO35RSB0
D16	NC
D17	NC
E1	VCCIB3
E2	IO114RSB3
E3	IO115RSB3
E4	IO118RSB3
E5	IO05RSB0
E6	NC

CS289	
Pin Number	AGLP030 Function
E7	IO06RSB0
E8	IO11RSB0
E9	IO22RSB0
E10	IO26RSB0
E11	VCCIB0
E12	NC
E13	IO33RSB0
E14	IO36RSB1
E15	IO38RSB1
E16	VCCIB1
E17	NC
F1	IO111RSB3
F2	NC
F3	IO116RSB3
F4	VCCIB3
F5	IO117RSB3
F6	NC
F7	NC
F8	IO08RSB0
F9	IO12RSB0
F10	NC
F11	NC
F12	NC
F13	NC
F14	GND
F15	NC
F16	IO37RSB1
F17	IO41RSB1
G1	IO110RSB3
G2	GND
G3	IO113RSB3
G4	NC
G5	NC
G6	NC
G7	GND
G8	GND
G9	VCC

CS289	
Pin Number	AGLP030 Function
G10	GND
G11	GND
G12	IO40RSB1
G13	NC
G14	IO39RSB1
G15	IO44RSB1
G16	NC
G17	GND
H1	NC
H2	GEC0/IO108RSB3
H3	NC
H4	IO112RSB3
H5	NC
H6	IO109RSB3
H7	GND
H8	GND
H9	GND
H10	GND
H11	GND
H12	NC
H13	NC
H14	IO45RSB1
H15	VCCIB1
H16	GDB0/IO48RSB1
H17	IO42RSB1
J1	NC
J2	GEA0/IO107RSB3
J3	VCCIB3
J4	IO105RSB3
J5	NC
J6	NC
J7	VCC
J8	GND
J9	GND
J10	GND
J11	VCC
J12	IO50RSB1

CS289	
Pin Number	AGLP030 Function
J13	IO43RSB1
J14	IO51RSB1
J15	IO52RSB1
J16	GDC0/IO46RSB1
J17	GDA0/IO47RSB1
K1	GND
K2	GEB0/IO106RSB3
K3	IO102RSB3
K4	IO104RSB3
K5	IO99RSB3
K6	NC
K7	GND
K8	GND
K9	GND
K10	GND
K11	GND
K12	NC
K13	NC
K14	NC
K15	IO53RSB1
K16	GND
K17	IO49RSB1
L1	IO103RSB3
L2	IO101RSB3
L3	NC
L4	GND
L5	NC
L6	NC
L7	GND
L8	GND
L9	VCC
L10	GND
L11	GND
L12	IO58RSB1
L13	IO54RSB1
L14	VCCIB1
L15	NC

CS289	
Pin Number	AGLP030 Function
L16	NC
L17	NC
M1	NC
M2	VCCIB3
M3	IO100RSB3
M4	IO98RSB3
M5	IO93RSB3
M6	IO97RSB3
M7	NC
M8	NC
M9	IO71RSB2
M10	NC
M11	IO63RSB2
M12	NC
M13	IO57RSB1
M14	NC
M15	NC
M16	NC
M17	VCCIB1
N1	NC
N2	NC
N3	IO95RSB3
N4	IO96RSB3
N5	GND
N6	NC
N7	IO85RSB2
N8	IO79RSB2
N9	IO77RSB2
N10	VCCIB2
N11	NC
N12	NC
N13	IO59RSB2
N14	NC
N15	GND
N16	IO56RSB1
N17	IO55RSB1
P1	IO94RSB3

Revision	Changes	Page
Revision 11 (continued)	The tables in the <a href="#">"Single-Ended I/O Characteristics"</a> section were updated. Notes clarifying IIL and IIH were added. Tables for 3.3 V LVCMOS and 1.2 V LVCMOS wide range were added (SAR 79370, SAR 79353, and SAR 79366). Notes in the wide range tables state that the minimum drive strength for any LVCMOS 3.3 V (or LVCMOS 1.2 V) software configuration when run in wide range is $\pm 100 \mu\text{A}$ . Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 25700).	2-27
	The following sentence was deleted from the <a href="#">"2.5 V LVCMOS"</a> section: It uses a 5 V–tolerant input buffer and push-pull output buffer (SAR 24916).	2-32
	The tables in the <a href="#">"Input Register"</a> section, <a href="#">"Output Register"</a> section, and <a href="#">"Output Enable Register"</a> section were updated. The tables in the <a href="#">"VersaTile Characteristics"</a> section were updated.	2-45 through 2-56
	The following tables were updated in the <a href="#">"Global Tree Timing Characteristics"</a> section: <a href="#">Table 2-85 • AGLP060 Global Resource (1.5 V)</a> <a href="#">Table 2-86 • AGLP125 Global Resource (1.5 V)</a> <a href="#">Table 2-88 • AGLP060 Global Resource (1.2 V)</a>	2-58
	<a href="#">Table 2-90 • IGLOO PLUS CCC/PLL Specification</a> and <a href="#">Table 2-91 • IGLOO PLUS CCC/PLL Specification</a> were revised (SAR 79388). VCO output jitter and maximum peak-to-peak jitter data were changed. Three notes were added to the table in connection with these changes.	2-61
	<a href="#">Figure 2-28 • Write Access after Write onto Same Address</a> and <a href="#">Figure 2-29 • Write Access after Read onto Same Address</a> were deleted.	N/A
	The tables in the <a href="#">"SRAM"</a> , <a href="#">"FIFO"</a> and <a href="#">"Embedded FlashROM Characteristics"</a> sections were updated.	2-68, 2-78

Revision	Changes	Page
<b>Revision 10 (Apr 2009)</b> Product Brief v1.5 DC and Switching Characteristics Advance v0.5	The –F speed grade is no longer offered for IGLOO PLUS devices. References to it have been removed from the document. The speed grade column and note regarding –F speed grade were removed from "IGLOO PLUS Ordering Information". The "Speed Grade and Temperature Grade Matrix" section was removed.	III, IV
<b>Revision 9 (Feb 2009)</b> Product Brief v1.4	The "Advanced I/O" section was revised to add two bullets regarding support of wide range power supply voltage.	I
	The "I/Os with Advanced I/O Standards" section was revised to add 3.0 V wide range to the list of supported voltages. The "Wide Range I/O Support" section is new.	1-7
<b>Revision 8 (Jan 2009)</b> Packaging v1.5	The "CS201" pin table was revised to add a note regarding pins G1 and H1.	4-8
<b>Revision 7 (Dec 2008)</b> Product Brief v1.3	A note was added to IGLOO PLUS Devices: "AGLP060 in CS201 does not support the PLL."	I
	Table 2 • IGLOO PLUS FPGAs Package Size Dimensions was updated to change the nominal size of VQ176 from 100 to 400 mm <sup>2</sup> .	II
<b>Revision 6 (Oct 2008)</b> DC and Switching Characteristics Advance v0.4	Data was revised significantly in the following tables: Table 2-25 • Summary of I/O Timing Characteristics—Software Default Settings, STD Speed Grade, Commercial-Case Conditions: T <sub>J</sub> = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings, STD Speed Grade Commercial-Case Conditions: T <sub>J</sub> = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V Table 2-50 • 2.5 LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage Table 2-51 • 2.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage	2-22, 2-33
<b>Revision 5 (Aug 2008)</b> Product Brief v1.2  Packaging v1.4	The VQ128 and VQ176 packages were added to Table 1 • IGLOO PLUS Product Family, the "I/Os Per Package" table, Table 2 • IGLOO PLUS FPGAs Package Size Dimensions, "IGLOO PLUS Ordering Information", and the "Temperature Grade Offerings" table.	I to IV
	The "VQ128" package drawing and pin table are new.	4-2
	The "VQ176" package drawing and pin table are new.	4-5
<b>Revision 4 (Jul 2008)</b> Product Brief v1.1 DC and Switching Characteristics Advance v0.3	As a result of the Libero IDE v8.4 release, Actel now offers a wide range of core voltage support. The document was updated to change 1.2 V / 1.5 V to 1.2 V to 1.5 V.	N/A
<b>Revision 3 (Jun 2008)</b> DC and Switching Characteristics Advance v0.2	Tables have been updated to reflect default values in the software. The default I/O capacitance is 5 pF. Tables have been updated to include the LVCMOS 1.2 V I/O set.	N/A
	Table note 3 was updated in Table 2-2 • Recommended Operating Conditions <sup>1,2</sup> to add the sentence, "VCCI should be at the same voltage within a given I/O bank." References to table notes 5, 6, 7, and 8 were added. Reference to table note 3 was removed from VPUMP Operation and placed next to VCC.	2-2
	Table 2-4 • Overshoot and Undershoot Limits <sup>1</sup> was revised to remove "as measured on quiet I/Os" from the title. Table note 2 was revised to remove "estimated SSO density over cycles." Table note 3 was deleted.	2-3